TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

2SC2782

VHF BAND POWER AMPLIFIER APPLICATIONS

Output Power : Po = 80W (Min.)

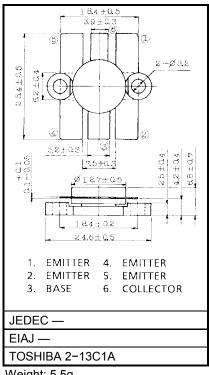
(f = 175MHz, V CC = 12.5V, Pi = 18W)

MAXIMUM RATINGS (Tc = 25°C)

CHARACTERISTIC SYMBOL		RATING	UNIT
Collector-Base Voltage	V _{CBO} 36 V		
Collector-Emitter Voltage	V _{CEO} 16 V		
Emitter-Base Voltage	V _{EBO} 4 V		
Collector Current	I _C 20		Α
Collector Power Dissipation	P _C 220 V	/	
Junction Temperature	T _j 175		°C
Storage Temperature Range	T _{stg}	−65~175 °C	



Unit in mm



Weight: 5.5g

In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..

The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal

equipment, office equipment, measuring equipment, intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, intended of the products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.

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The information contained herein is subject to change without notice.

TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devicesin general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury o damage to property.

ELECTRICAL CHARACTERISTICS (Tc = 25°C)

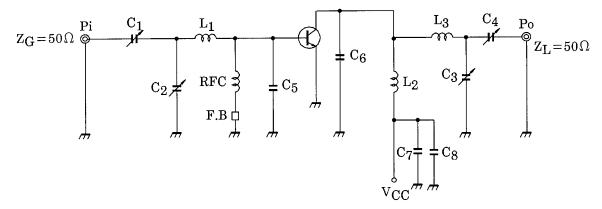
CHARACTERISTIC SYMBOL		TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Base Breakdown Voltage	V (BR) CBO	I _C = 20mA, I _E = 0	36	_	_	V
Collector-Emitter Breakdown Voltage	V (BR) CEO	I _C = 50mA, I _B = 0	16	_	_	V
Emitter-Base Breakdown Voltage	V (BR) EBO	I _E = 1mA, I _C = 0	4	_	_	V
DC Current Gain	h _{FE} V	_{CE} = 5V, I _C = 10A *	10	_	_	
Collector Output Capacitance	C _{ob}	$V_{CB} = 12.5V, I_{E} = 0$ f = 1MHz		320		pF
Output Power	P _o 80	(Fig.) V _{CC} = 12.5V, f = 175MHz		90	— W	
Power Gain	G _p 6.4			6.8	— dB	
Collector Efficiency	η _C	Pi = 18W	60 7	0 — %		
Series Equivalent Input Impedance	Z _{in} —	V _{CC} = 12.5V		1.0 +j1.5	_	Ω
Series Equivalent Output Impedance	Z _{out}	f = 175MHz, Po = 80W	_	1.2 +j1.8	_	Ω

^{*} Pulse Test: Pulse Width ≤ 100µs, Duty Cycle ≤ 3%

CAUTION

Beryllia Ceramics is used in this product. The dust or vapor can be dangerous to humans. Do not break, cut, crush or dissolve chemically. Dispose of this product properly according to law. Do not intermingle with normal industrial or domestic waste.

Fig. Po TEST CIRCUIT



 $C_1 \sim C_4$: $\sim 20 pF$

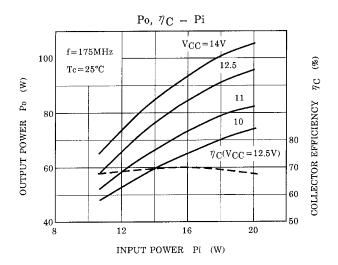
 C_5 : $156pF(39pF\times4)$ CERAMIC CONDENSER C_6 : $132pF(33pF\times4)$ CERAMIC CONDENSER

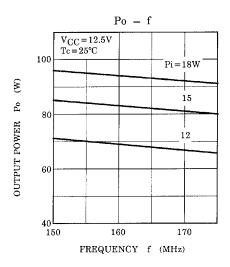
C₇ : 0.01μF CERAMIC CONDENSER

 C_8 : $10\mu F$

L₁, L₃ : ϕ 1.5mm SILVER PLATED COPPER WIRE, 10ID, 1T L₂ : ϕ 1.5mm SILVER PLATED COPPER WIRE, 10ID, 2T RFC : ϕ 1mm ENAMEL COATED COPPER WIRE, 6ID, 10T

FB : FERRITE BEAD





CAUTION

These are only typical curves and devices are not necessarily guaranteed at these curves.